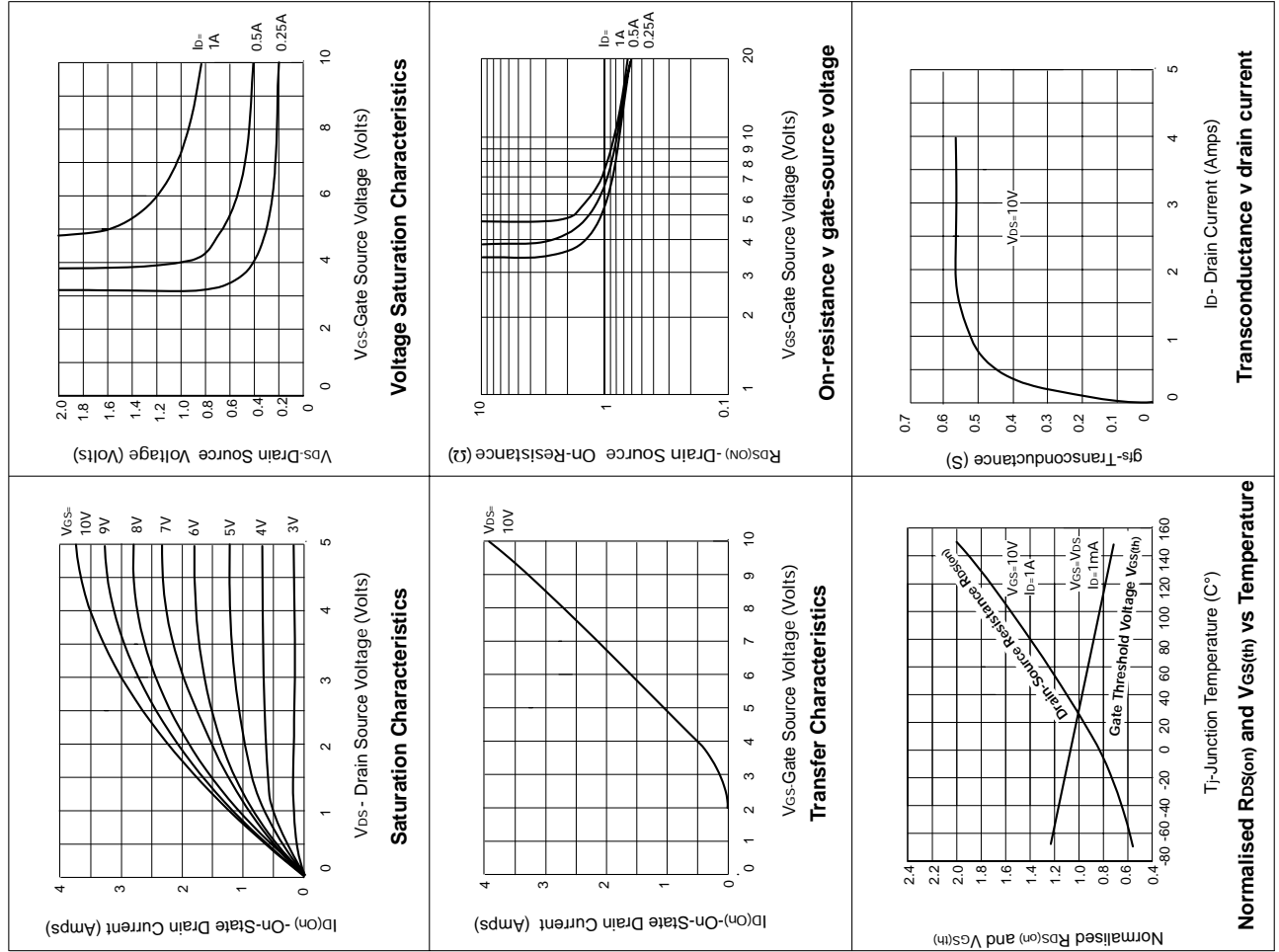


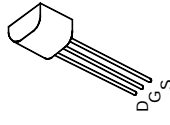
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TYPICAL CHARACTERISTICS



FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 2\Omega$



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

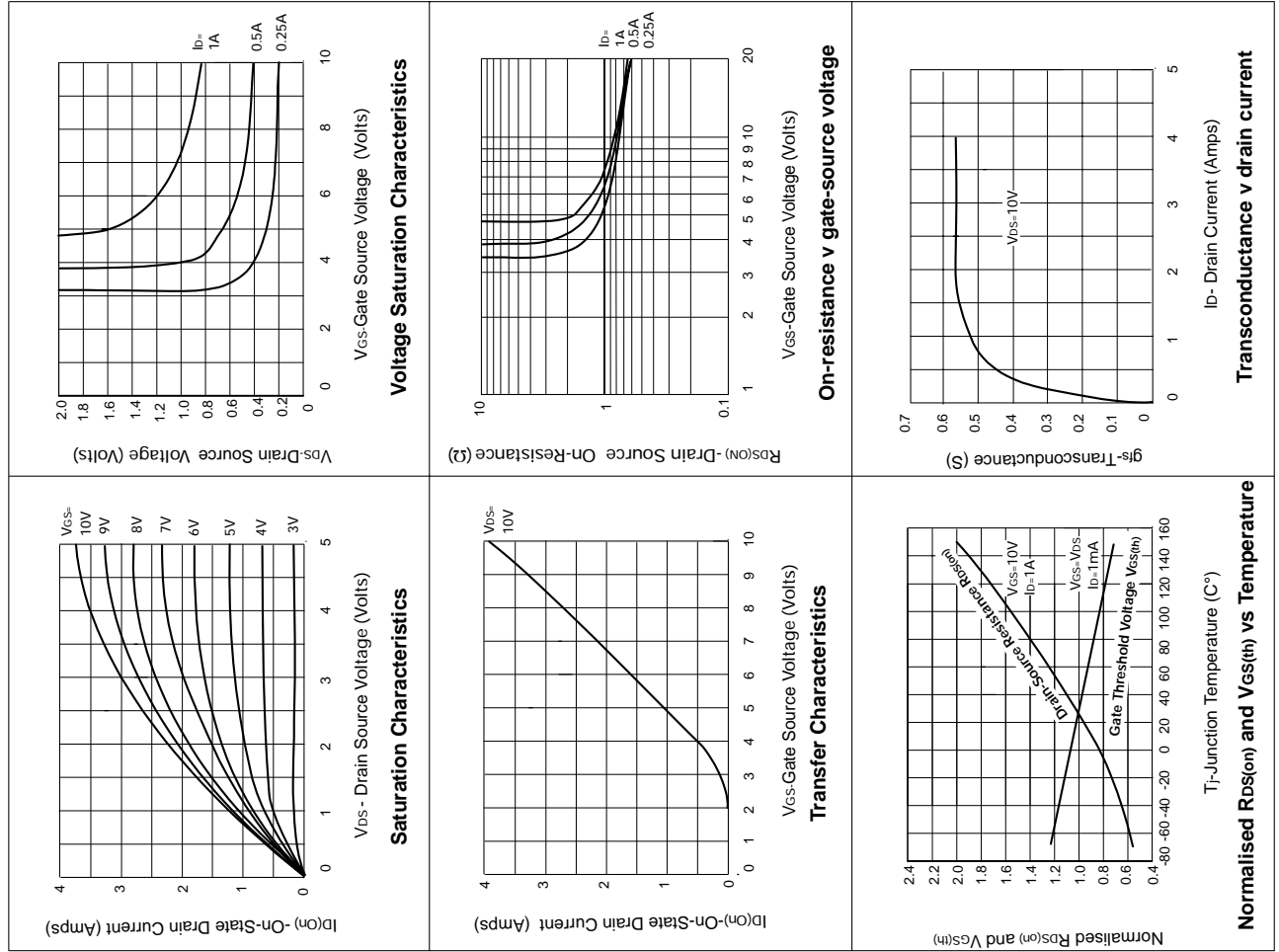
PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	60	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	I_D	450	mA
Pulsed Drain Current	I_{DM}	8	A
Gate Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	700	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	60		V	$I_D = 1mA, V_{GS} = 0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D = 1mA, V_{DS} = V_{GS}$
Gate-Body Leakage	I_{GSS}		20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Zero Gate Voltage Drain Current	I_{DSS}		500 100	nA μA	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 48V, V_{GS} = 0V,$ $T = 125^{\circ}C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2		A	$V_{DS} = 18V, V_{GS} = 10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		2	Ω	$V_{GS} = 10V, I_D = 1A$
Forward Transconductance (1)(2)	g_{fs}	300		mS	$V_{DS} = 18V, I_D = 1A$
Input Capacitance (2)	C_{iss}		75	pF	
Common Source Output Capacitance (2)	C_{oss}		45	pF	$V_{DS} = 18V, V_{GS} = 0V, f = 1MHz$
Reverse Transfer Capacitance (2)	C_{rss}		20	pF	

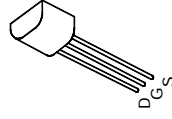
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TYPICAL CHARACTERISTICS

